

## N-Channel Enhancement Mode Power MOSFET

### Description

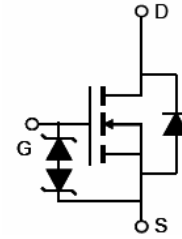
The AO3416 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.

### General Features

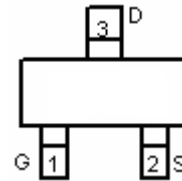
- $V_{DS} = 20V, I_D = 6A$   
 $R_{DS(ON)} < 26m\Omega @ V_{GS}=2.5V$   
 $R_{DS(ON)} < 22m\Omega @ V_{GS}=4.5V$   
 ESD Rating: 2000V HBM
- High Power and current handing capability
- Lead free product is acquired
- Surface mount package

### Application

- PWM application
- Load switch



Schematic diagram



Marking and pin Assignment



SOT-23-3L top view

### Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	±12	V
Drain Current-Continuous	$I_D$	6	A
Drain Current-Pulsed (Note 1)	$I_{DM}$	30	A
Maximum Power Dissipation	$P_D$	1.4	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	89.3	°C/W
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### Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	20		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V, V_{GS}=0V$	-	-	1	μA

Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	$\pm 10$	$\mu A$
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.7	1.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=6A$	-	17	22	$m\Omega$
		$V_{GS}=2.5V, I_D=5A$	-	21	26	$m\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=4.5A$	11	-	-	S
<b>Dynamic Characteristics (Note4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0MHz$	-	660	-	PF
Output Capacitance	$C_{oss}$		-	160	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	87	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, R_L=1.5\Omega$ $V_{GS}=5V, R_{GEN}=3\Omega$	-	0.5		nS
Turn-on Rise Time	$t_r$		-	1		nS
Turn-Off Delay Time	$t_{d(off)}$		-	12		nS
Turn-Off Fall Time	$t_f$		-	4		nS
Total Gate Charge	$Q_g$	$V_{DS}=10V, I_D=6A,$ $V_{GS}=4.5V$	-	8		nC
Gate-Source Charge	$Q_{gs}$		-	2.5	-	nC
Gate-Drain Charge	$Q_{gd}$		-	3	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=1A$	-	-	1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	6	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

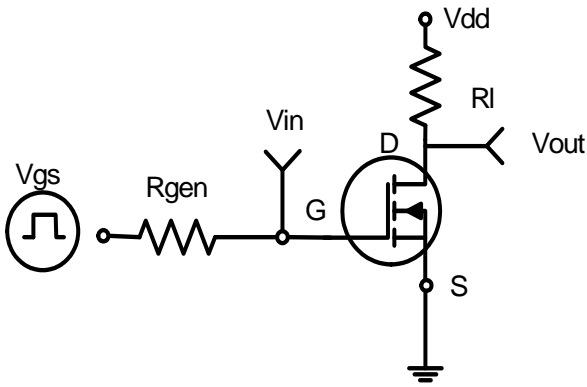


Figure 1: Switching Test Circuit

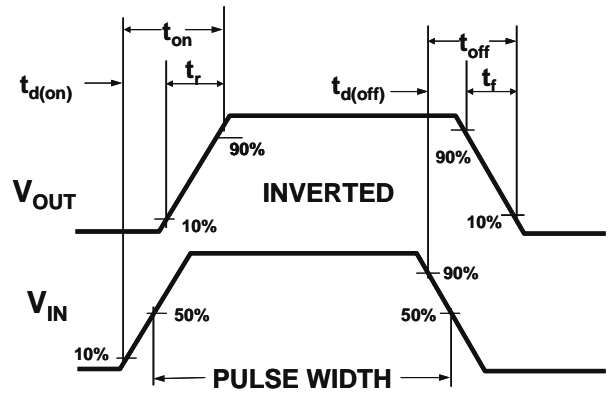


Figure 2: Switching Waveforms

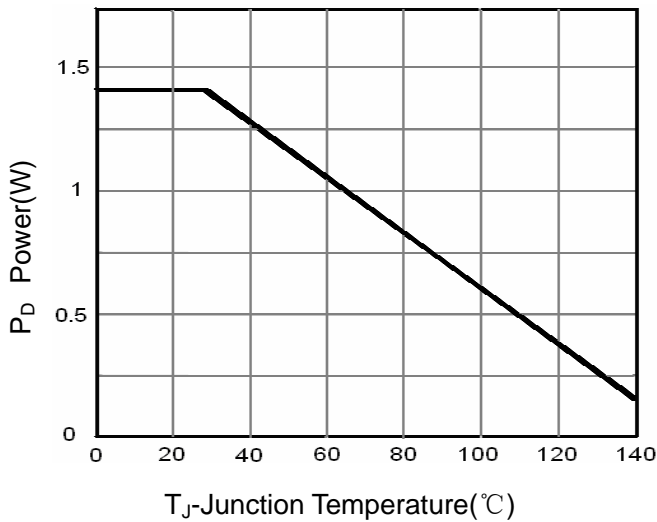


Figure 3 Power Dissipation

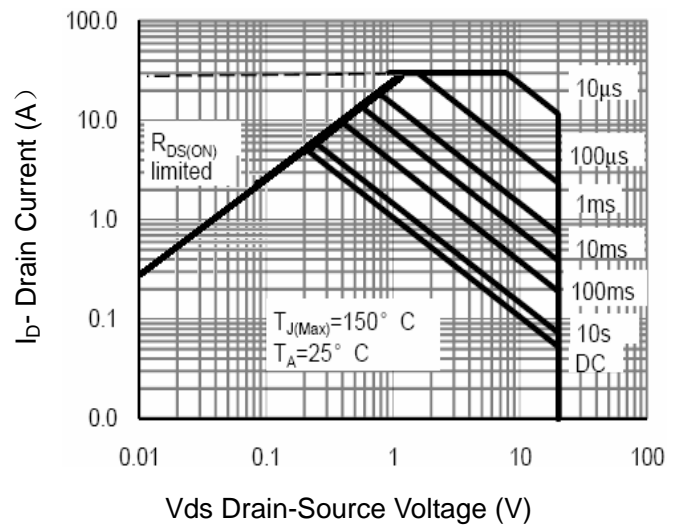


Figure 4 Safe Operation Area

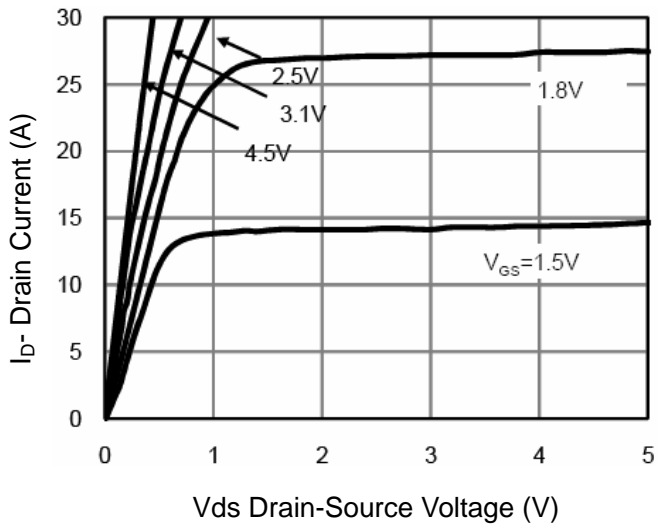


Figure 5 Output CHARACTERISTICS

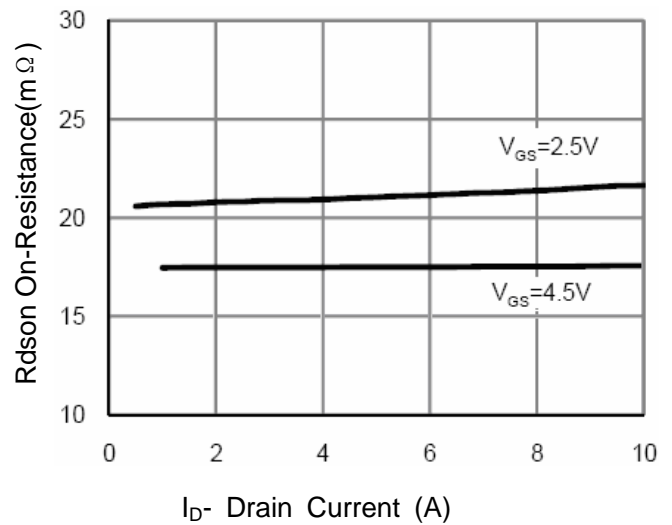


Figure 6 Drain-Source On-Resistance

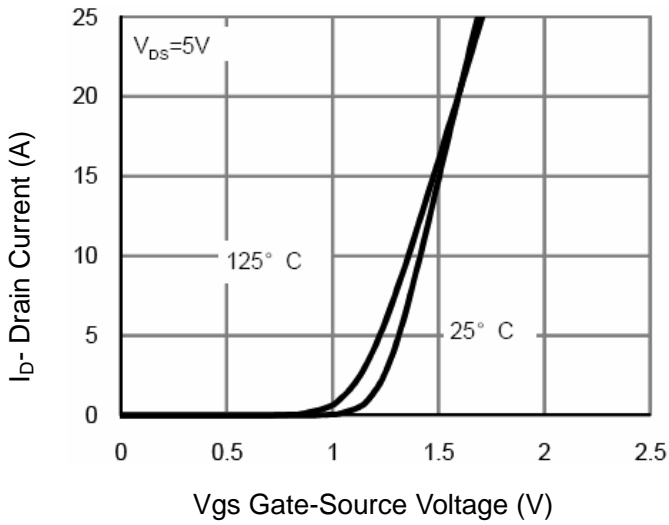


Figure 7 Transfer Characteristics

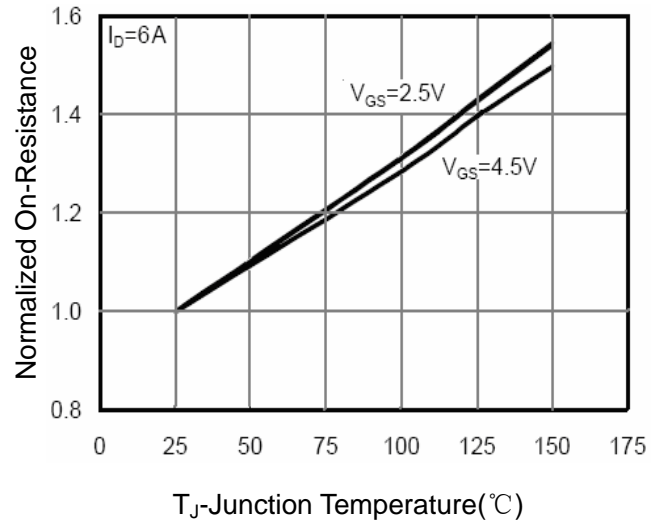


Figure 8 Drain-Source On-Resistance

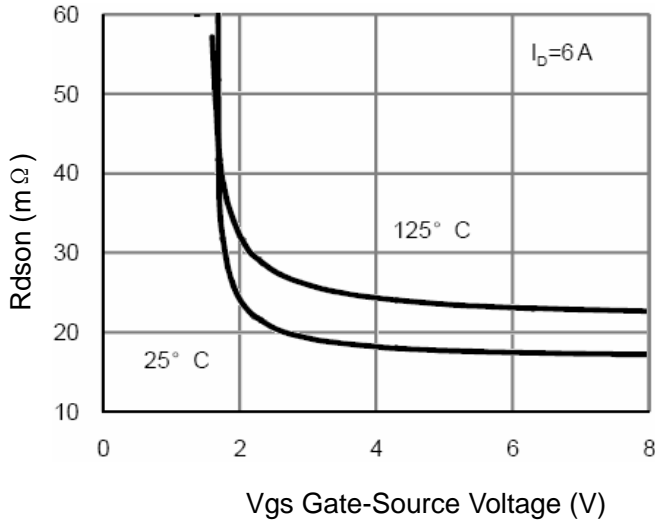


Figure 9 Rdson vs Vgs

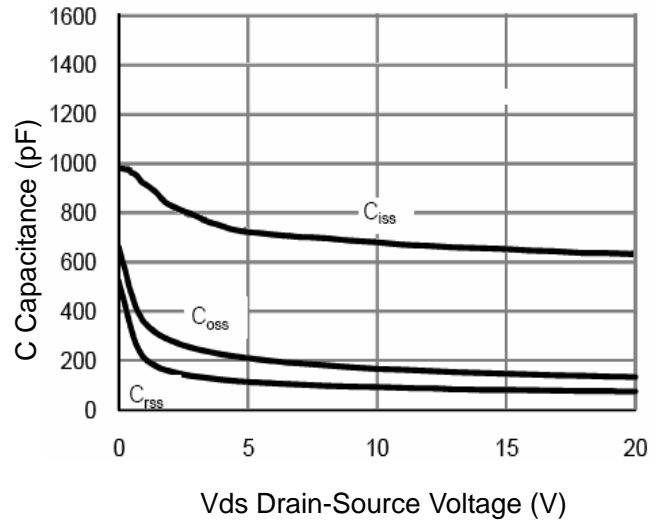


Figure 10 Capacitance vs Vds

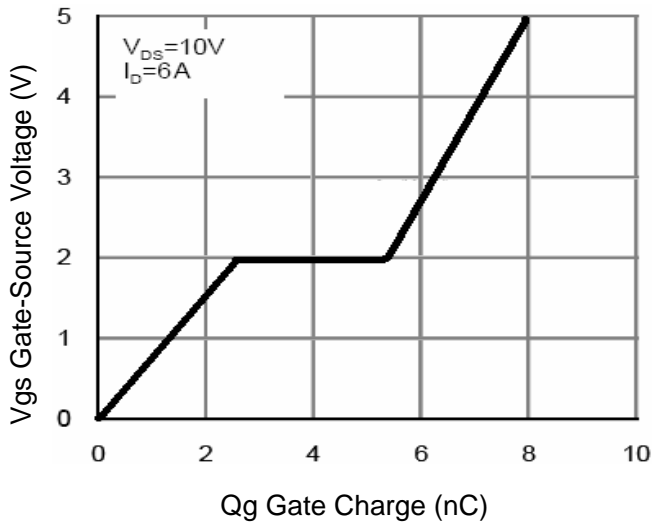


Figure 11 Gate Charge

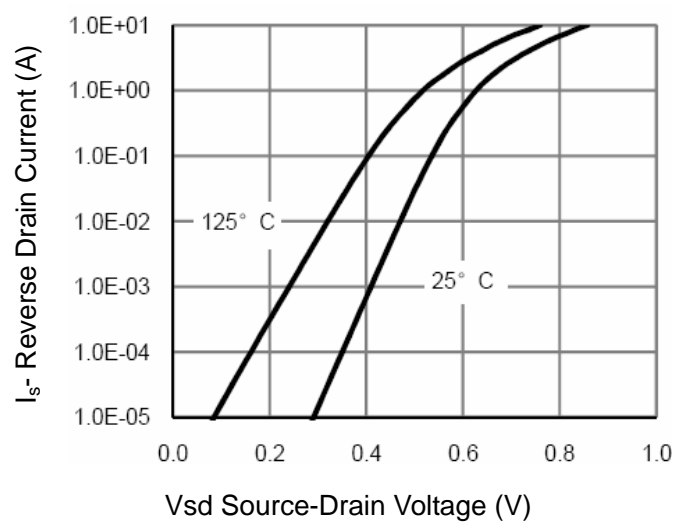


Figure 12 Source- Drain Diode Forward

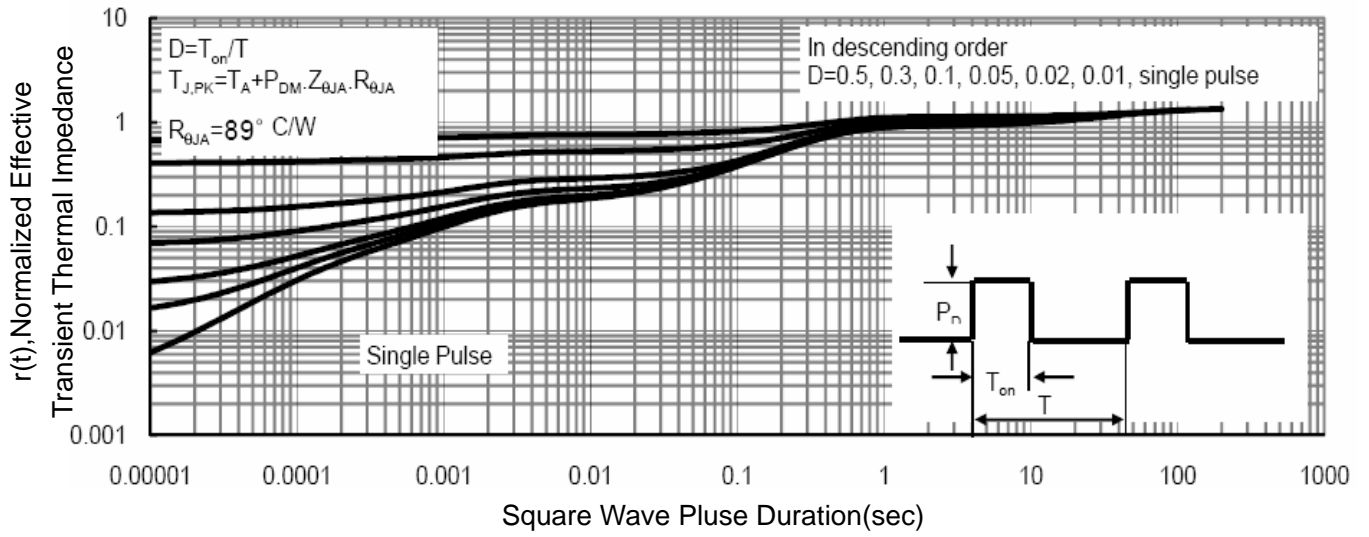


Figure 13 Normalized Maximum Transient Thermal Impedance